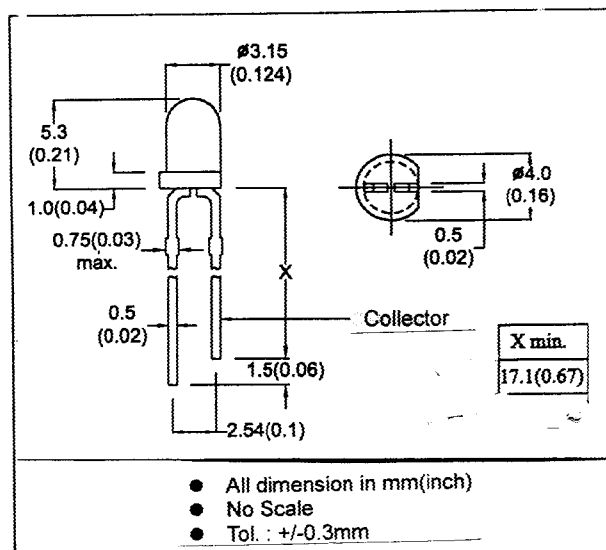


DESCRIPTION

MDL78 is NPN silicon planar photo-darlington transistor. It features ultra high illumination sensitivity, fast response time.



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	10V
Emitter-Collector Voltage	V _{ECO}	4V
Continuous Power Dissipation	P _d	50mW
Operating Junction Temperature	T _j	-40 to +85°C
Storage Temperature Range	T _{stg}	-40 to +100°C
Lead Soldering Temperature (5 sec., 1/16" from body)		260°C for 5 sec.

ELECTRO-OPTICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CEO}	10			V	I _C =100μA E _e =0
Emitter-Collector Breakdown Voltage	BV _{ECO}	4			V	I _C =100μA E _e =0
Dark Current	I _D			2	μA	V _{CE} =10V E _e =0
Light Current	I _L *				mA	V _{CE} =5V E _e =5mW/cm ²
Group A		16		86		
Group B		32		160		
Group C		64		320		
Collector-Emitter Saturation Voltage	V _{CE(sat)}			1.2	V	I _C =15mA I _B =100μA
Rise Time	T _r		40		μs	V _{CC} =5V I _C =10mA R _L =100Ω
Fall Time	T _f		60		μs	V _{CC} =5V I _C =10mA R _L =100Ω



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